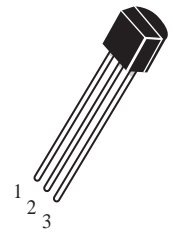


NPN Silicon General Purpose Transistors

 Lead(Pb)-Free

TO-92

1. EMITTER
2. BASE
3. COLLECTOR


MAXIMUM RATINGS* $T_A=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CB0}	Collector-Base Voltage	310	V
V_{CEO}	Collector-Emitter Voltage	305	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	500	mA
T_J, T_{stg}	Junction and Storage Temperature	-55-150	$^{\circ}\text{C}$
$R_{\theta JA}$	Thermal Resistance, junction to Ambient	200	$^{\circ}\text{C}/\text{mW}$
$R_{\theta JC}$	Thermal Resistance, junction to Case	83.3	$^{\circ}\text{C}/\text{mW}$

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

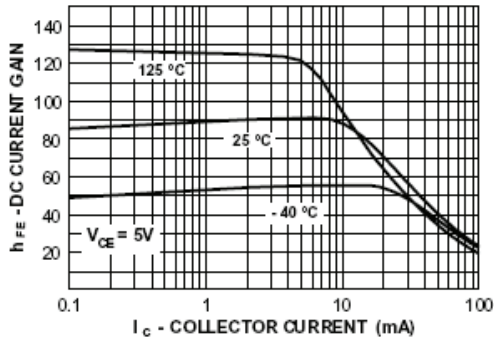
ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	310			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	305			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu\text{A}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=200\text{V}, I_E=0$			0.25	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=10\text{V}, I_C=1\text{mA}$	60			
	$h_{FE(2)}$	$V_{CE}=10\text{V}, I_C=10\text{mA}$	80		250	
	$h_{FE(3)}$	$V_{CE}=10\text{V}, I_C=30\text{mA}$	75			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=20\text{mA}, I_B=2\text{mA}$			0.2	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=20\text{mA}, I_B=2\text{mA}$			0.9	V
Transition frequency	f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=30\text{MHz}$	50			MHz

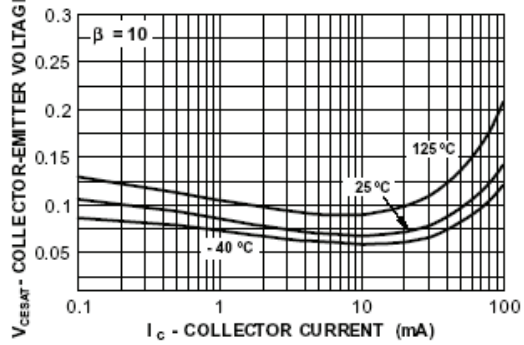
CLASSIFICATION OF $h_{FE(2)}$

Rank	A	B ₁	B ₂	C
Range	80-100	100-150	150-200	200-250

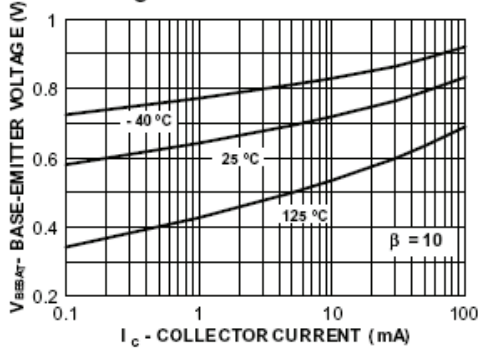
DC Current Gain vs Collector Current



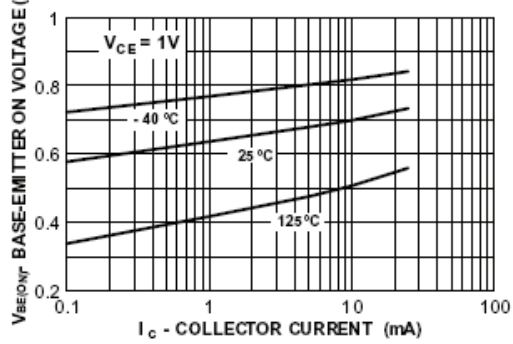
Collector-Emitter Saturation Voltage vs Collector Current



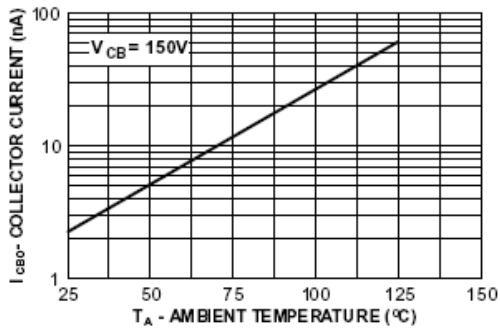
Base-Emitter Saturation Voltage vs Collector Current



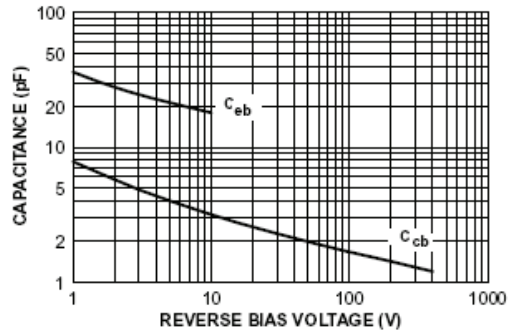
Base-Emitter ON Voltage vs Collector Current



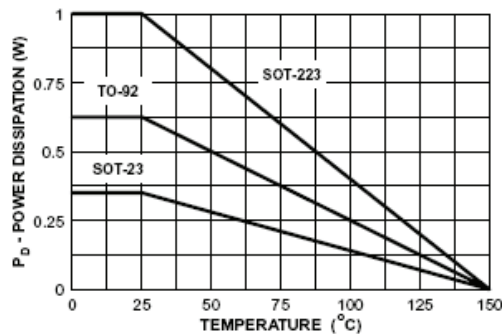
Collector-Cutoff Current vs Ambient Temperature



Collector-Base and Emitter-Base Capacitance vs Reverse Bias Voltage

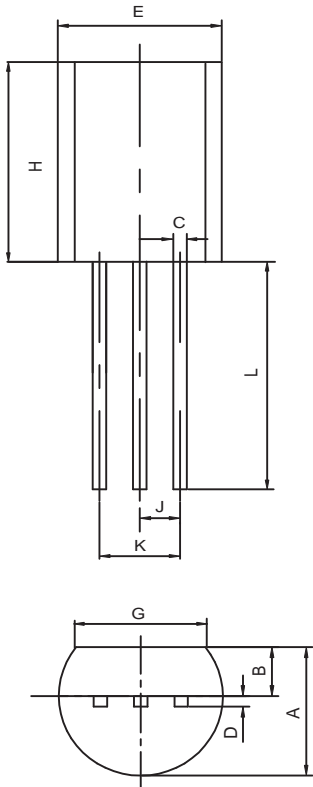


Power Dissipation vs Ambient Temperature



TO-92 Outline Dimensions

unit:mm



TO-92		
Dim	Min	Max
A	3.30	3.70
B	1.10	1.40
C	0.38	0.55
D	0.36	0.51
E	4.40	4.70
G	3.43	-
H	4.30	4.70
J	1.270TYP	
K	2.44	2.64
L	14.10	14.50